

MDL-III-830 /100~2000mW

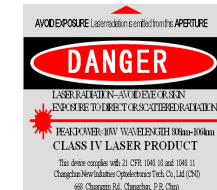
SPECIFICATIONS

INFRARED DIODE LASER AT 830nm

Infrared diode laser at 830nm is made features of high power, long lifetime, low cost and easy operating, which is widely used in measurement, spectrum analysis, etc.



Wavelength (nm)	830±10		
Output power (mW)	>100, 150, 200, ..., 2000		
Transverse mode	Near TE ₀₀		
Operating mode	CW		
Power stability (rms, over 4 hours)	<1%, <3%, <5%		
Warm-up time (minutes)	<5		
Beam divergence, full angle (mrad)	<2.5		
Dimensions of beam at the aperture (mm)	~5×8		
Beam height from base plate (mm)	24.8		
Operating temperature (°C)	10~35		
Power supply (90-264VAC)	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
TTL modulation/ Analog modulation	Optional, 2kHz or higher (others on request, up to 30kHz)		
Expected lifetime (hours)	10000		
Warranty	1 year		



MxL-III-830	PSU-III-LED	PSU-III-FDA	PSU-III-OEM
<p>140. 8(L)×73(W)×46. 2(H) mm³, 0.6kg</p>	<p>154 (L) ×155(W) ×95 (H) mm³, 1.5kg</p>	<p>133 (L) ×130(W) ×65 (H) mm³, 1.2kg</p>	<p>100 (L) ×60(W) ×56 (H) mm³, 0.2kg</p>